

Appl. No. 10/652,007  
Amendment dated May 20, 2005  
Reply to Office Action of February 23, 2005

**Amendments to the Specification:**

On page 1, line 6 (after the heading **CROSS REFERENCE TO RELATED APPLICATIONS**), please replace all of the paragraphs under this heading with the following rewritten paragraphs:

This application is a division of U.S. Patent Application Serial No. 09/792,691 filed February 23, 2001[[]] now U.S. Patent No. 6,649,219 B2, issued November 18, 2003.

The subject matter of this application relates to the subject matter of U.S. Patent 6,572,925, entitled "A PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION", assigned to the assignee of this application, and filed on the same date as the parent application of this application.

The subject matter of this application relates to the subject matter of ~~copending~~ U.S. Patent ~~Application~~ Serial No. 6,858,195, issued February 22, 2005, 09/792,685, entitled "A PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION", assigned to the assignee of this application, and filed on the same date as the parent application of this application.

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The subject matter of this application relates to the subject matter of U.S. Patent No. 6,365,528, issued April 2, 2002, entitled "A LOW TEMPERATURE PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION AND GOOD GAP-FILLING CAPABILITIES", and assigned to the assignee of this application.

Please replace the paragraph beginning at page 19, line 29, with the following rewritten paragraph:

Similarly, the low k fluorine and carbon-containing silicon oxide dielectric material formed in the method of the invention may find utility, for example, as one or more of the low k dielectric layers described in U.S. Patent Nos. 6,423,628, issued July 23, 2002; 6,232,658, issued May 15, 2001; 6,391,795, issued May 21, 2002; 6,492,731, issued December 10, 2002; 6,350,700, issued February 26, 2002; 6,423,630, issued July 23, 2002; and 6,537,923, issued March 25, 2003; and 6,756,674, issued June 29, 2004; Serial No. 09/426,061; all assigned to the assignee of this invention.